

AMENDMENTS TO THE CLAIMS

Please replace the claims, including all prior versions, with the listing of claims below.

Listing of Claims:

1. (Currently amended) ~~Method~~A method for masking first recesses (1) in a structure (4) having webs (4) with a high aspect ratio, comprising a set of recesses (1, 2) having different aspect ratios, ~~in particular a semiconductor structure, having the following steps comprising:~~
 - ~~_____ applying a filling layer (5) is applied~~ to the structure (1, 2, 4), with the filling layer (5) ~~being~~ applied over a fixed distance beyond the webs (4) in such a way that a cavity (6) is formed in the first recesses (1) having a high aspect ratio;;
 - ~~_____ removing the filling layer (5) is removed~~ by means of a planar removal process into ~~the~~an area of the cavity (6) with the filling layer (5) ~~being~~ removed to a defined distance above ~~the~~a surface of the webs (4);;
 - ~~_____ removing the filling layer (5) is removed~~ in an etching process, with the etching process ~~also~~ attacking in the cavity (6) and, owing to the cavity (6), the filling layer (5) ~~being~~ removed more quickly from the first recess (1) than from recesses (2) without a cavity (6), and ~~with~~ the etching process being stopped after removal of the filling layer (5) from the first recess (1), with the defined distance being ~~chosen~~selected such that the webs (4) are not underetched in ~~the~~an area of a recess (2) with a low aspect ratio during the etching process.

2. (Currently amended) ~~Method~~The method according to Claim 1, ~~characterized in that~~wherein an isotropic etching method is used as the etching method.

3. (Currently amended) ~~Method~~The method according to ~~one of Claims 1 or 2,~~ ~~characterized in that~~claim 1, wherein the structure (1, 2, 4) has the webs (4), and ~~in that~~ a sacrificial layer (12) is applied to the surface of the webs (4), before the application of the filling layer (5).

4. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 3,~~ characterized in that claim 1, wherein a chemical/mechanical polishing method is used as ~~the~~ a planar removal process.

5. (Currently amended) ~~Method~~ The method according to Claim 4, characterized in that wherein the defined distance is chosen to be greater than twice ~~the~~ a maximum thickness (β) of the filling material (~~5~~) between ~~at~~ the cavity (~~6~~) and the structure (~~4, 3~~).

6. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 5,~~ characterized in that claim 1, wherein the structure (~~1, 2, 4~~) is formed from a silicon wafer (~~3~~).

7. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 6,~~ characterized in that claim 1, wherein a silicon oxide is deposited as the filling layer (~~5~~), using a TEOS process.

8. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 7,~~ characterized in that claim 1, wherein silicon oxide is deposited as the sacrificial layer (~~12~~).

9. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 8,~~ characterized in that claim 1, wherein the filling layer (~~5~~) is applied over a recess (~~2~~) with a low aspect ratio to above ~~the~~ a height of the cavity (~~6~~).